

PATENT ABSTRACTS OF JAPAN

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(21)Application number : 09-281754 (71)Applicant : TEXAS INSTR
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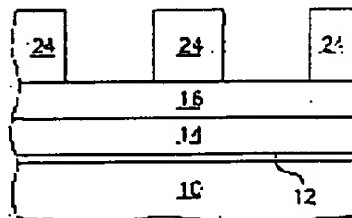
(54) SEMICONDUCTOR TREATMENT METHOD

(57)Abstract:

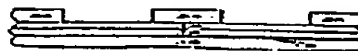
PROBLEM TO BE SOLVED: To provide
an optical assist layer for
optimizing a profile of resist
patterns.

SOLUTION: A pad oxide 12 and a
nitride layer 14 are formed on a
substrate, and an optical assist
layer 16 is formed before
deposition of resist.

Thereafter, a resist layer is
deposited to form resist
patterns 24. These resist
patterns 24 have a straight
sidewall due to presence of the



optical assist layer 16 and does not form a resist 'foot' under the resist patterns 24. A



thickness of the optical assists layer 16 is optimized so as to reduce/remove interference between the resist layer and a substrate 10, and accordingly the resist 'foot' is reduced/removed.

LEGAL STATUS

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